

AMENDMENTS TO THE CLAIMS

1. (Original) A method comprising:
removing material from a surface of a wafer by chemical mechanical polishing the wafer with a slurry comprising an oxidation agent for the material and a buffer; and
monitoring the current required to rotate the wafer as a measure of the material removal endpoint.
2. (Original) The method of Claim 1, further comprising:
buffering with a weak organic acid/salt pair.
3. (Original) The method of Claim 2, further comprising:
buffering with a weak organic acid/salt from the group consisting of citric acid/potassium citrate, acetic acid/potassium acetate and ascorbic acid/potassium ascorbate.
4. (Original) A composition comprising:
a slurry for chemical mechanical polishing a metal material;
an oxidizing agent for the metal material;
an abrasive; and
a buffer;
wherein the composition is suitable for use in a chemical mechanical polish process.
5. (Original) The composition of Claim 4, wherein the oxidizing agent is hydrogen peroxide.
6. (Original) The composition of Claim 4, wherein the buffer is a weak organic acid/salt pair.
7. (Original) The composition of Claim 6, wherein the weak organic acid comprises one of the group consisting of citric acid/potassium citrate, acetic acid/potassium acetate and ascorbic acid/potassium ascorbate.

8. (Currently Amended) The composition of Claim 4, wherein the metal ~~film~~material comprises one of the group consisting of tungsten and titanium nitride.
9. (Canceled)
10. (Original) The composition of Claim 4, wherein the abrasive comprises one of the group consisting of silica and alumina.
11. (Currently Amended) The composition of Claim 4, wherein the endpoint signal of the ~~buffered-slurry~~composition is enhanced over ~~the~~an endpoint signal of ~~the-unbuffered~~a composition comprising a slurry, an oxidizing agent, and an abrasive and without a buffer by at least a factor of two.
12. (Currently Amended) A kit comprising:
a slurry for chemical mechanical polishing a metal material;
an oxidizing agent for the metal material;
an abrasive; and
a buffer;
wherein the slurry, the oxidizing agent, the abrasive, and the buffer are to be combined into a polish suitable for a chemical mechanical polish operation.
13. (Currently Amended) The kit of Claim 12, wherein the metal material comprises one of the group consisting of tungsten and tantalum nitride.
14. (Original) The kit of Claim 12, wherein the abrasive comprises one of the group consisting of silica or alumina.
15. (Original) The kit of Claim 12, wherein the buffer is an organic acid/salt pair.

16. (Original) The kit of Claim 15, wherein the organic acid comprises one of the group consisting of citric acid/potassium citrate, acetic acid/potassium acetate and ascorbic acid/potassium ascorbate.

17. (Currently Amended) The kit of Claim 12, wherein the endpoint signal of the ~~buffered slurry~~polish is enhanced over the endpoint signal of ~~the unbuffered~~a polish comprising a slurry, an oxidizing agent, and an abrasive and without a buffer by at least a factor of two.